

N- and P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY				
	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
N-Channel	60	0.025 at V _{GS} = 10 V	22	23
		0.029 at V _{GS} = 4.5 V	20	
P-Channel	- 60	0.041 at V _{GS} = - 10 V	- 19	42
		0.053 at V _{GS} = - 4.5 V	- 16	

FEATURES

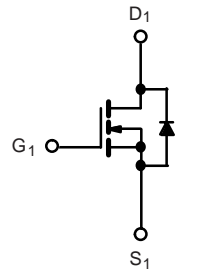
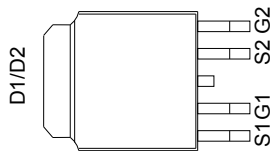
- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested



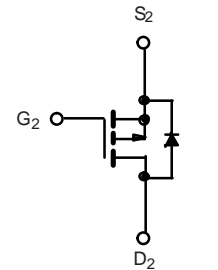
APPLICATIONS

- Inverter

TO-252-4L



N-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter	Symbol	N-Channel	P-Channel	Unit	
Drain-Source Voltage	V _{DS}	60	- 60	V	
Gate-Source Voltage	V _{GS}	± 20	± 20		
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	22	- 19	A
		T _C = 70 °C	20	- 15	
		T _A = 25 °C	8.0 ^{b, c}	- 7.2 ^{b, c}	
		T _A = 70 °C	6.2 ^{b, c}	- 5.8 ^{b, c}	
Pulsed Drain Current (10 μs Pulse Width)	I _{DM}	88	- 76	A	
Source-Drain Current Diode Current	I _S	T _C = 25 °C	22		- 19
		T _A = 25 °C	18 ^{b, c}	- 16 ^{b, c}	
Pulsed Source-Drain Current	I _{SM}	88	- 76	mJ	
Single Pulse Avalanche Current	I _{AS}	20	- 18		
Single Pulse Avalanche Energy	E _{AS}	35	57	W	
Maximum Power Dissipation	P _D	T _C = 25 °C	56		69
		T _C = 70 °C	32		52
		T _A = 25 °C	g ^{b, c}		8 ^{b, c}
		T _A = 70 °C	7.28 ^{b, c}	6.59 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	N-Channel		P-Channel		Unit
		Typ.	Max.	Typ.	Max.	
Maximum Junction-to-Ambient ^{b, d}	R _{thJA}	19	25	20	30	°C/W
Maximum Junction-to-Foot (Drain)	R _{thJF}	40	50	40	50	

Notes:

a. Based on T_C = 25 °C.

b. Surface Mounted on 1" x 1" FR4 board.

c. t = 10 s.

d. Maximum under Steady State conditions is 120 °C/W (N-Channel) and 110 °C/W (P-Channel).

SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted								
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit		
Static								
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	N-Ch	60			V	
		$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	P-Ch	-60				
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\ \mu\text{A}$	N-Ch		40		mV/°C	
		$I_D = -250\ \mu\text{A}$	P-Ch		-40			
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250\ \mu\text{A}$	N-Ch		-4.1			
		$I_D = -250\ \mu\text{A}$	P-Ch		5.0			
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	N-Ch	1.0		3.0	V	
		$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	P-Ch	-1.0		-3.0		
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	N-Ch			± 100	nA	
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	P-Ch			± 100		
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 48\text{ V}, V_{GS} = 0\text{ V}$	N-Ch			1	μA	
		$V_{DS} = -48\text{ V}, V_{GS} = 0\text{ V}$	P-Ch			-1		
		$V_{DS} = 48\text{ V}, V_{GS} = 0\text{ V}, T_J = 55^\circ\text{C}$	N-Ch			10		
		$V_{DS} = -48\text{ V}, V_{GS} = 0\text{ V}, T_J = 55^\circ\text{C}$	P-Ch			-10		
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	N-Ch	22			A	
		$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	P-Ch	-19				
Drain-Source On-State Resistance ^b	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 8\text{ A}$	N-Ch		0.025	0.030	Ω	
		$V_{GS} = -10\text{ V}, I_D = -8\text{ A}$	P-Ch		0.041	0.051		
		$V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$	N-Ch		0.029	0.038		
		$V_{GS} = -4.5\text{ V}, I_D = -5\text{ A}$	P-Ch		0.053	0.065		
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 8\text{ A}$	N-Ch		27		S	
		$V_{DS} = -15\text{ V}, I_D = -8\text{ A}$	P-Ch		25			
Dynamic^a								
Input Capacitance	C_{iss}	N-Channel $V_{DS} = 48\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	N-Ch		755		pF	
Output Capacitance	C_{oss}		P-Ch		1050			
Reverse Transfer Capacitance	C_{rss}	P-Channel $V_{DS} = 48\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	N-Ch		120			
			P-Ch		240			
Total Gate Charge	Q_g	$V_{DS} = 48\text{ V}, V_{GS} = 10\text{ V}, I_D = 10\text{ A}$	N-Ch		23		nC	
		$V_{DS} = -48\text{ V}, V_{GS} = -10\text{ V}, I_D = -10\text{ A}$	P-Ch		42			
		N-Channel $V_{DS} = 48\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$	N-Ch		16			
			P-Ch		21.7			
Gate-Source Charge	Q_{gs}	P-Channel $V_{DS} = -48\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -10\text{ A}$	N-Ch		2.6			
Gate-Drain Charge	Q_{gd}		P-Ch		5.6			
Gate Resistance	R_g	$f = 1\text{ MHz}$	N-Ch	0.3	1.5	3.0		Ω
			P-Ch	1.3	6.4	12.8		

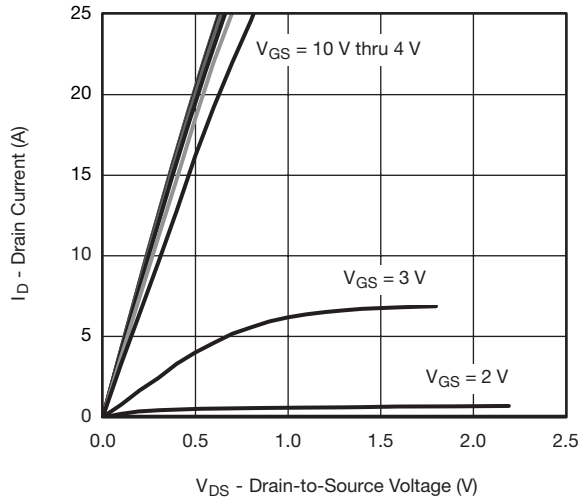
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted									
Parameter	Symbol	Test Conditions		Min.	Typ. ^a	Max.	Unit		
Dynamic^a									
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 48\text{ V}, R_L = 2\ \Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\ \Omega$	N-Ch		7	14	ns		
Rise Time	t_r		P-Ch		9	18			
Turn-Off Delay Time	$t_{d(off)}$	P-Channel $V_{DD} = -48\text{ V}, R_L = 2\ \Omega$ $I_D \cong -10\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\ \Omega$	N-Ch		10	20			
			P-Ch		9	18			
Fall Time	t_f		N-Ch		18	36			
			P-Ch		50	90			
Turn-On Delay Time	$t_{d(on)}$		N-Channel $V_{DD} = 48\text{ V}, R_L = 2\ \Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\ \Omega$	N-Ch		9		18	
				P-Ch		14		28	
Rise Time	t_r			N-Ch		11	22		
				P-Ch		42	75		
Turn-Off Delay Time	$t_{d(off)}$	P-Channel $V_{DD} = -48\text{ V}, R_L = 2\ \Omega$ $I_D \cong -10\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\ \Omega$		N-Ch		15	30		
				P-Ch		40	70		
Fall Time	t_f			N-Ch		23	46		
				P-Ch		40	70		
				N-Ch		13	26		
				P-Ch		15	30		
Drain-Source Body Diode Characteristics									
Continuous Source-Drain Diode Current	I_S			$T_C = 25\text{ }^\circ\text{C}$	N-Ch			22	A
Pulse Diode Forward Current ^a	I_{SM}			P-Ch			-19		
Body Diode Voltage	V_{SD}	$I_S = 2\text{ A}$ $I_S = -2\text{ A}$		N-Ch		0.7	1.2	V	
				P-Ch		-0.7	-1.2		
Body Diode Reverse Recovery Time	t_{rr}	N-Channel $I_F = 5\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		N-Ch		17	34	ns	
Body Diode Reverse Recovery Charge	Q_{rr}		P-Ch		30	60			
Reverse Recovery Fall Time	t_a	P-Channel $I_F = -5\text{ A}, dI/dt = -100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$	N-Ch		10	20	nC		
			P-Ch		26	52			
Reverse Recovery Rise Time	t_b		N-Ch		10		ns		
			P-Ch		15				
				N-Ch		7			
				P-Ch		15			

Notes:

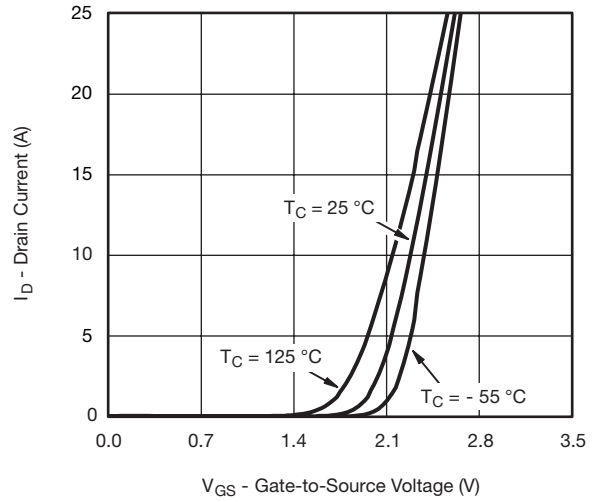
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

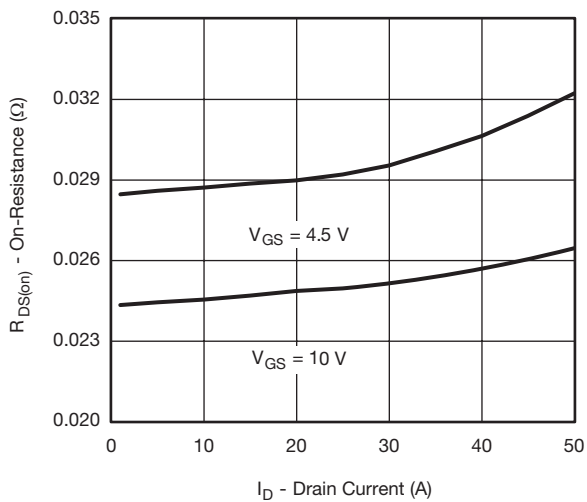
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



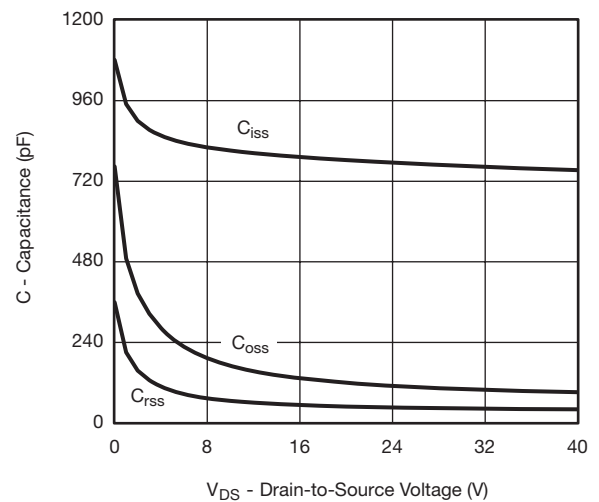
Output Characteristics



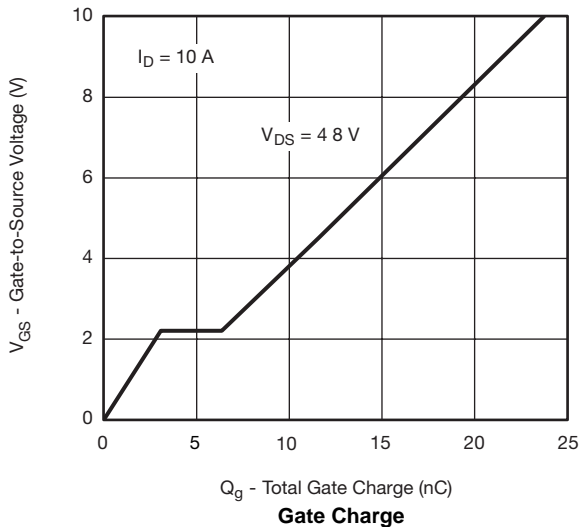
Transfer Characteristics



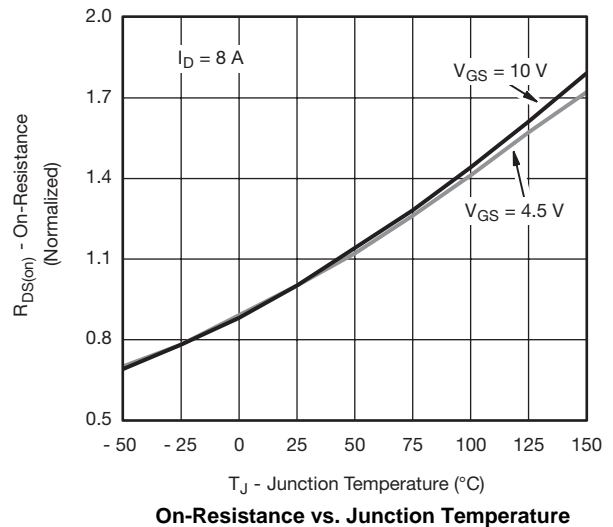
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

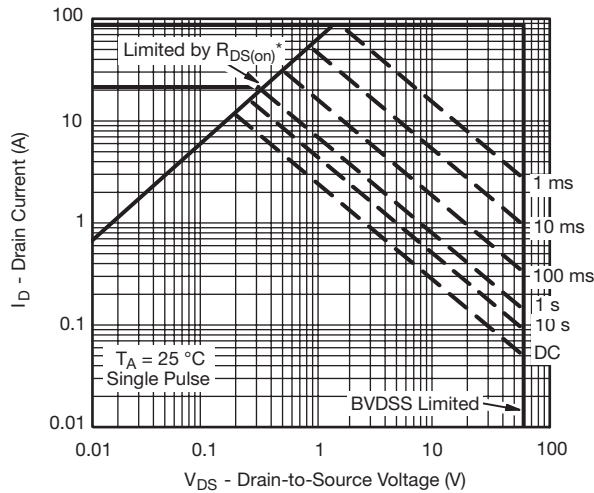
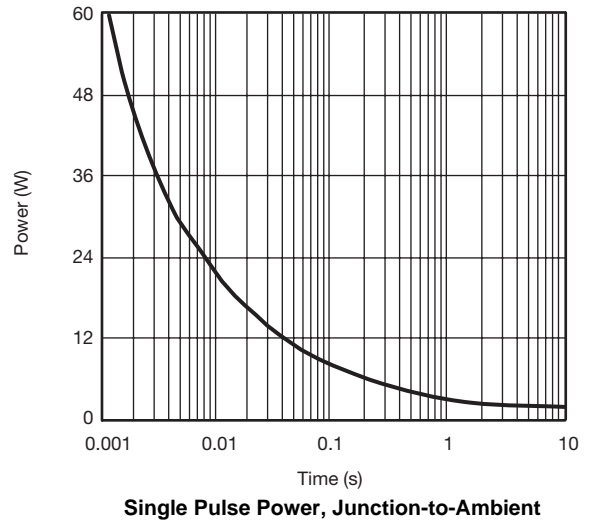
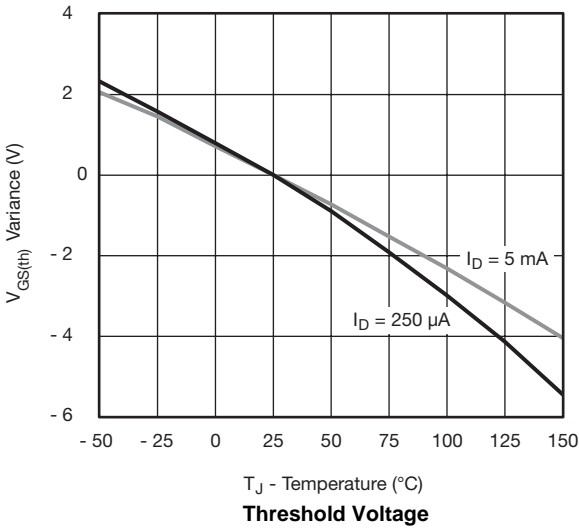
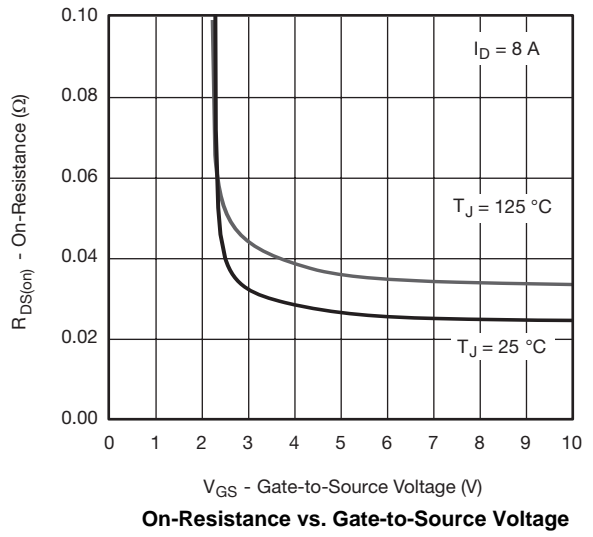
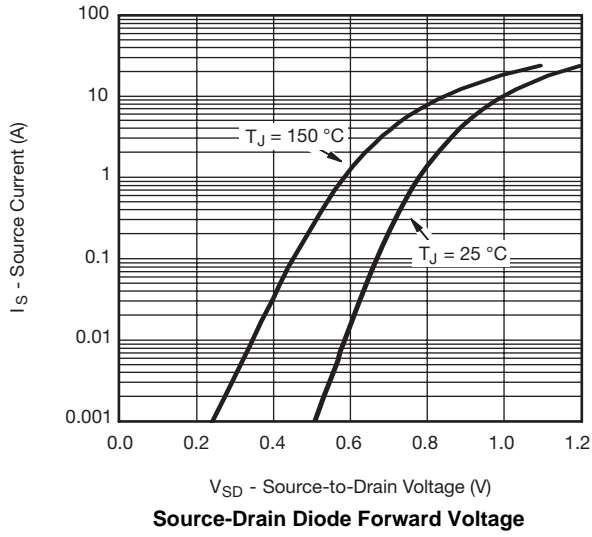


Gate Charge



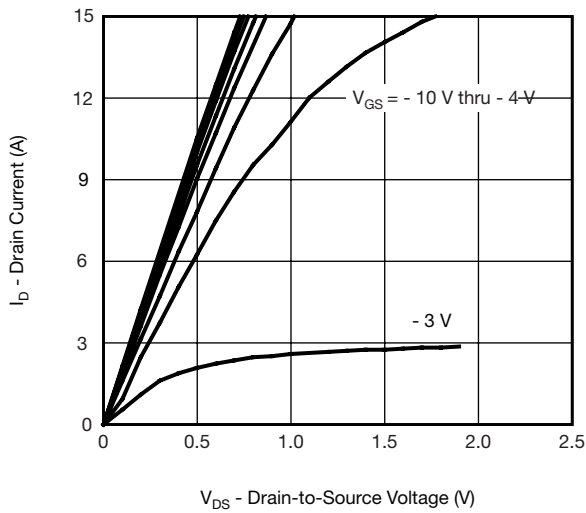
On-Resistance vs. Junction Temperature

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

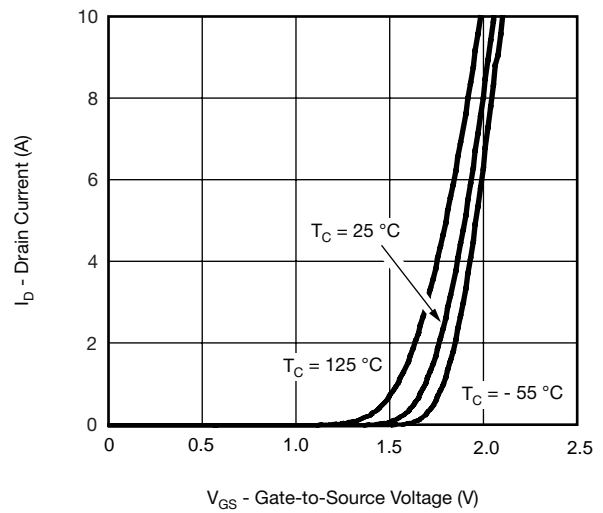


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

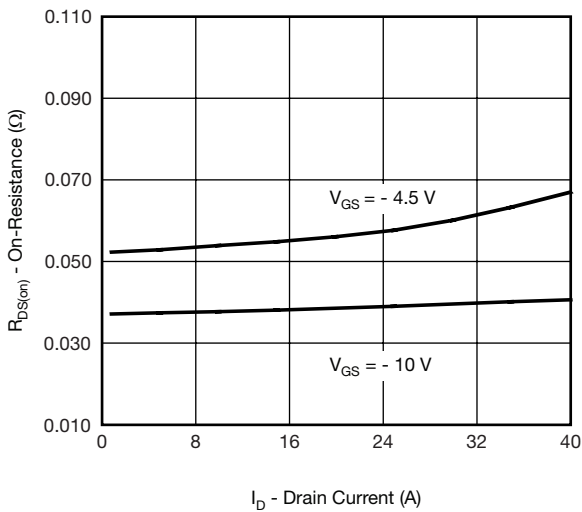
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



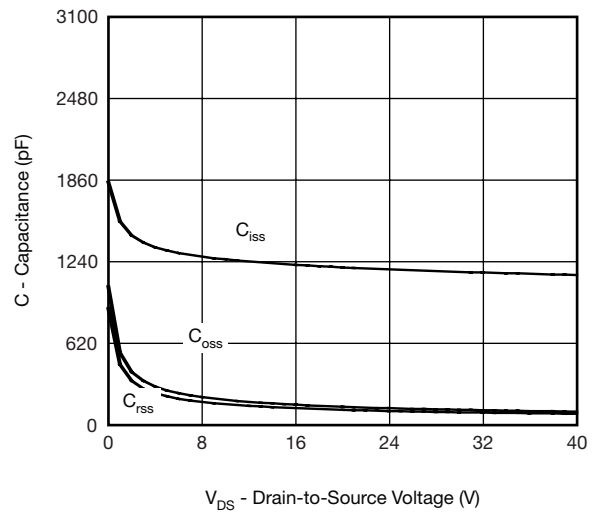
Output Characteristics



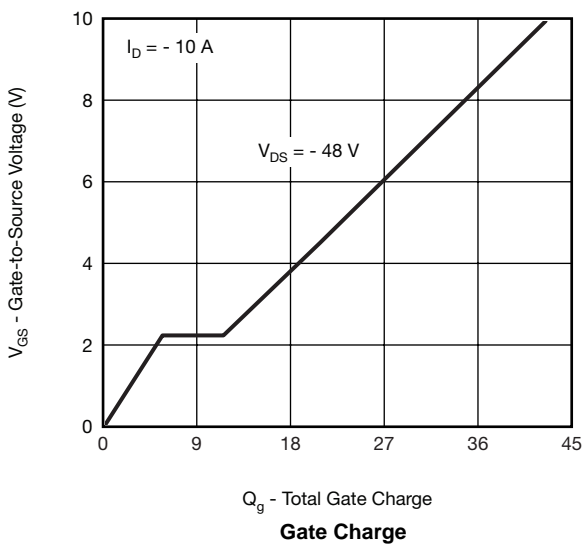
Transfer Characteristics



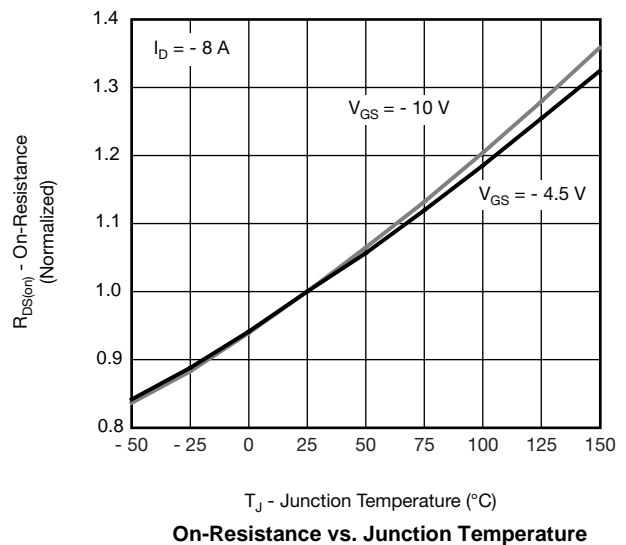
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

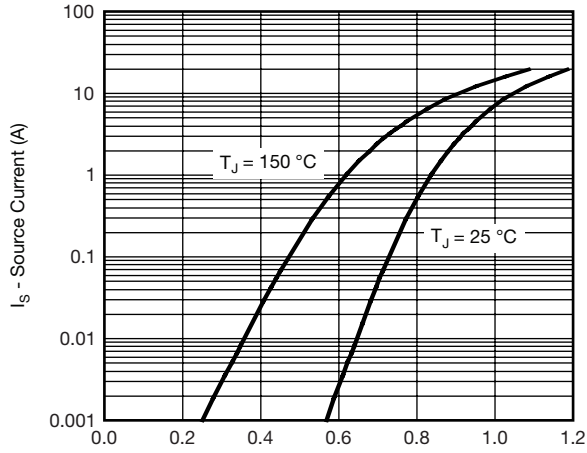


Gate Charge



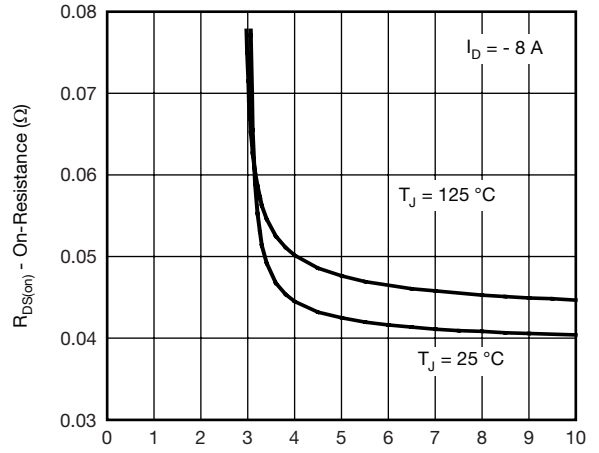
On-Resistance vs. Junction Temperature

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



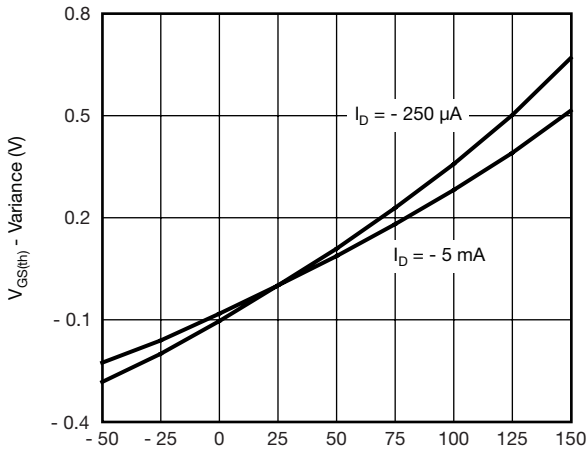
V_{SD} - Source-to-Drain Voltage (V)

Source-Drain Diode Forward Voltage



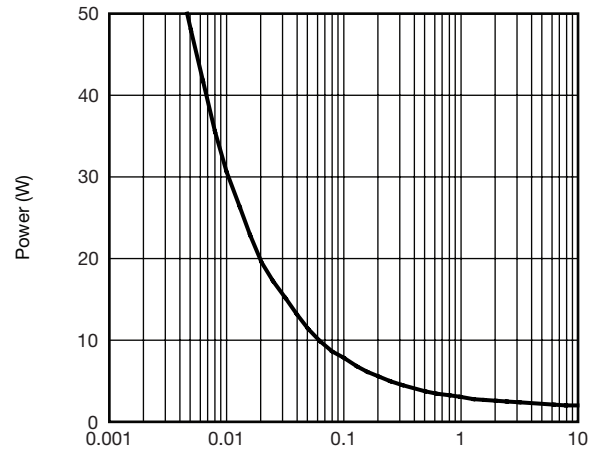
V_{GS} - Gate-to-Source Voltage (V)

On-Resistance vs. Gate-to-Source Voltage



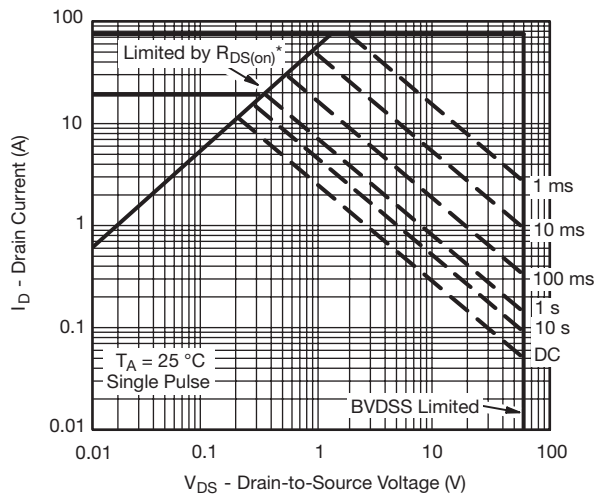
T_J - Junction Temperature ($^\circ\text{C}$)

Threshold Voltage



Time (s)

Single Pulse Power, Junction-to-Ambient

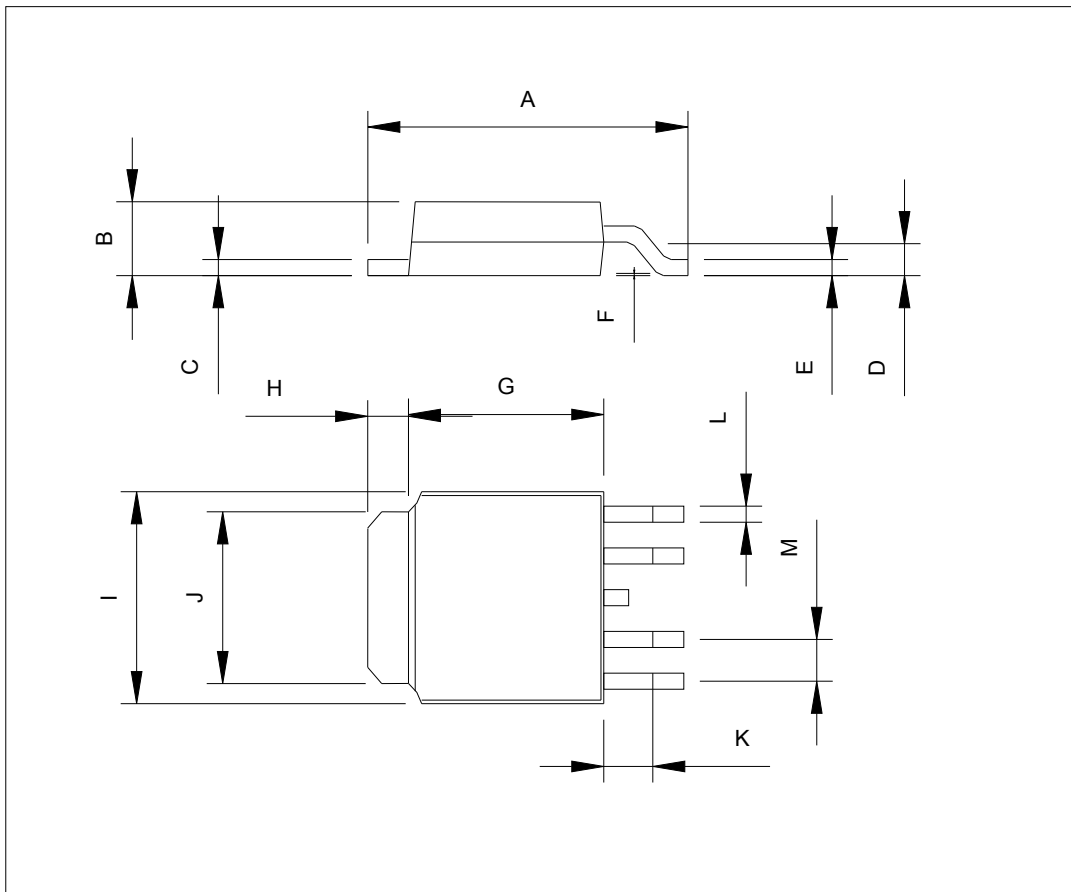


* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

TO-252 (DPAK): 4-LEAD

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	8.8	9.5	10.9	H	1.2	1.5	1.8
B	1.9	2.3	2.6	I	6.0	6.5	7.0
C	0.4	0.5	0.6	J	4.5	5.0	5.5
D	1.1	1.2	1.3	K	0.8	1.3	1.8
E	0.3	0.5	0.6	L	0.3	0.5	0.7
F	0.00		0.3	M	1.1	1.3	1.5
G	5.0	5.5	6.0	N			



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